Silicon PNP Power Transistors 2SA1633

DESCRIPTION

- With TO-247 package
- Complement to type 2SC4278
- High current and high power capability

APPLICATIONS

- For audio output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

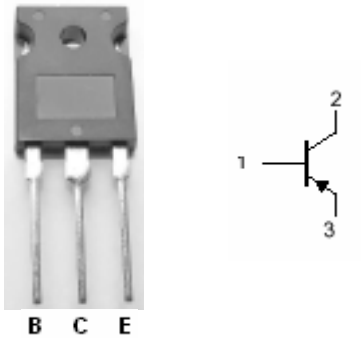


Fig.1 simplified outline (TO-247) and

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-10	A
P_D	Total power dissipation	T_C=25℃	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-25mA; I_B=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A ;I_B=-0.5A			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-5A ;I_B=-0.5A			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-0.1	mA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-5V	60		320	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		20		MHz

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320

PACKAGE OUTLINE

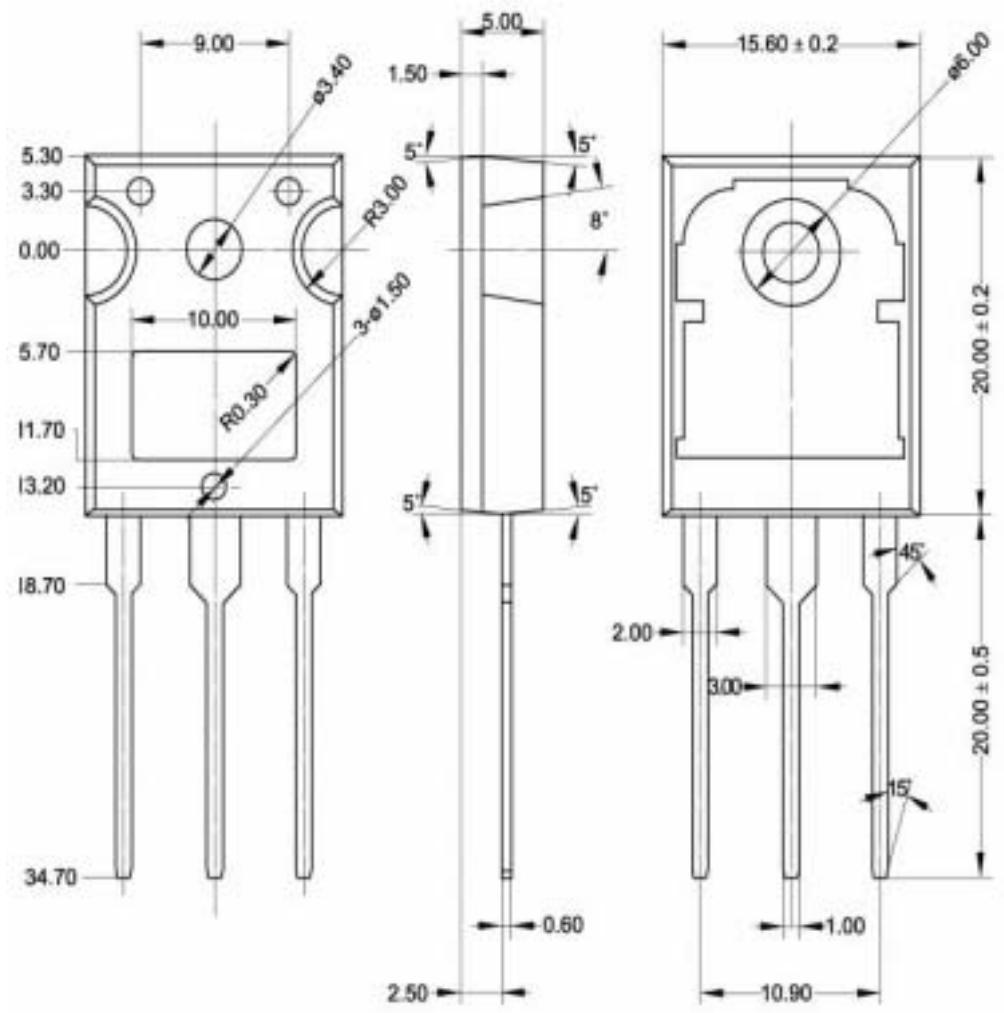


Fig.2 Outline dimensions